

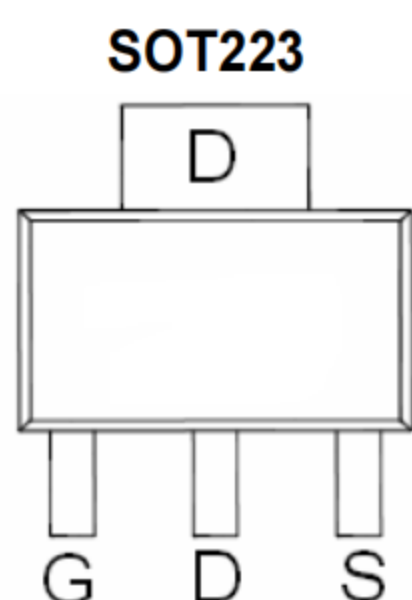
### GENERAL FEATURES

- 60V, 4A,  $R_{DS(ON)} = 85m\Omega$  @  $V_{GS} = 10V$ .  
 $R_{DS(ON)} = 100m\Omega$  @  $V_{GS} = 4.5V$ .
- High dense cell design for extremely low  $R_{DS(ON)}$ .
- Rugged and reliable.
- Lead free product is acquired.
- SOT-223 package.

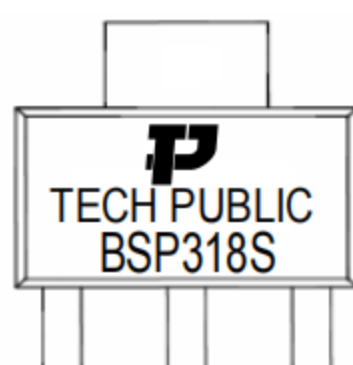
### Application

- Load/Power Switching
- Interfacing Switching
- Logic Level Shift

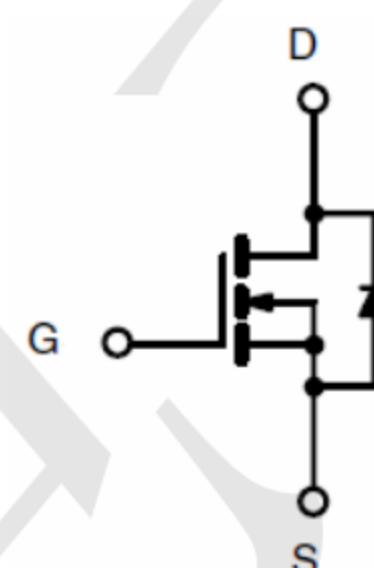
### Package and Pin Configuration



### Marking:



### Circuit diagram



### ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ C$ unless otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	$V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	4	A
Drain Current-Pulsed <sup>a</sup>	$I_{DM}$	20	A
Maximum Power Dissipation	$P_D$	3	W
Operating and Store Temperature Range	$T_J, T_{stg}$	-55 to 150	$^\circ C$

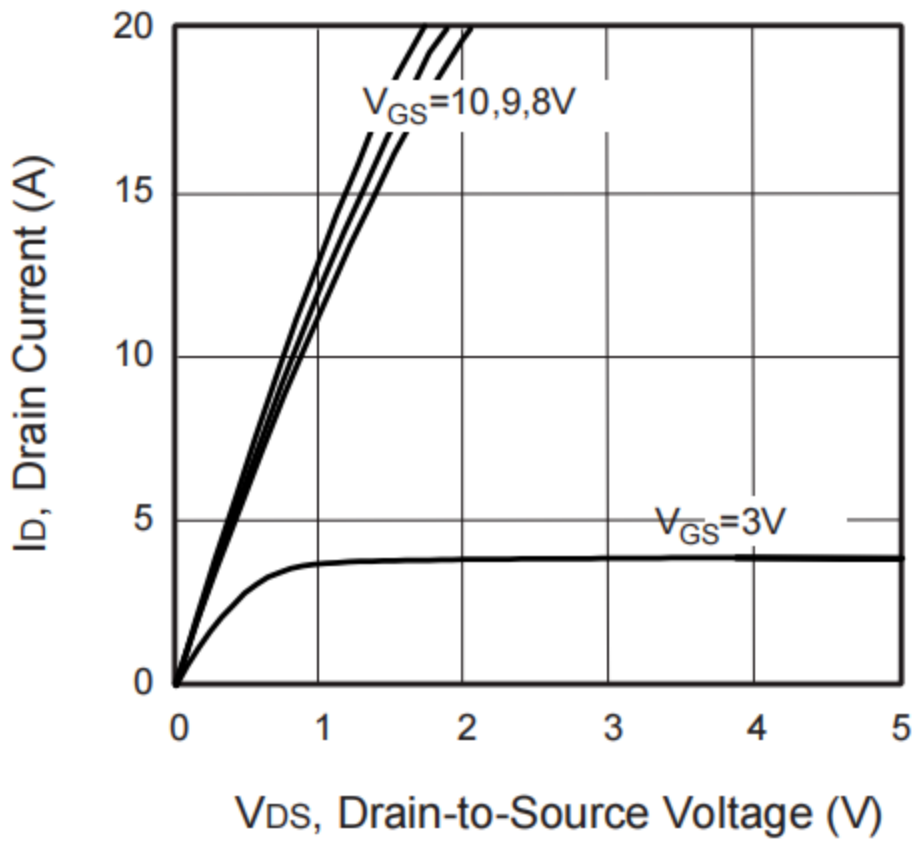
### Thermal Characteristics

Parameter	Symbol	Limit	Units
Thermal Resistance, Junction-to-Ambient <sup>b</sup>	$R_{\theta JA}$	42	$^\circ C/W$

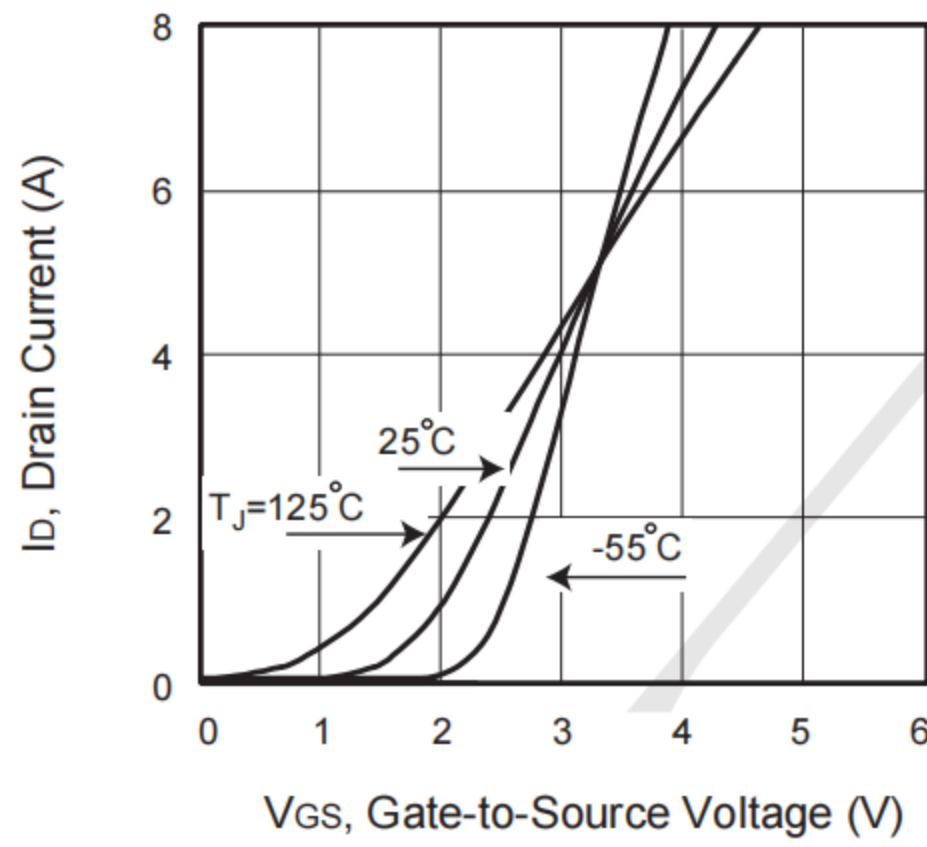
### Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	60			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 60V, V_{GS} = 0V$			1	$\mu A$
Gate Body Leakage Current, Forward	$I_{GSSF}$	$V_{GS} = 20V, V_{DS} = 0V$			100	nA
Gate Body Leakage Current, Reverse	$I_{GSSR}$	$V_{GS} = -20V, V_{DS} = 0V$			-100	nA
<b>On Characteristics</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	1		3	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 2A$			85	$m\Omega$
		$V_{GS} = 4.5V, I_D = 1.5A$			100	$m\Omega$
<b>Dynamic Characteristics<sup>d</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0\text{ MHz}$		530		pF
Output Capacitance	$C_{oss}$			70		pF
Reverse Transfer Capacitance	$C_{rss}$			50		pF
<b>Switching Characteristics<sup>d</sup></b>						
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 30V, I_D = 1A, V_{GS} = 10V, R_{GEN} = 6\Omega$		9	18	ns
Turn-On Rise Time	$t_r$			4	8	ns
Turn-Off Delay Time	$t_{d(off)}$			28	56	ns
Turn-Off Fall Time	$t_f$			3	6	ns
Total Gate Charge	$Q_g$	$V_{DS} = 30V, I_D = 4.5A, V_{GS} = 10V$		13	17	nC
Gate-Source Charge	$Q_{gs}$			1		nC
Gate-Drain Charge	$Q_{gd}$			4		nC
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
Drain-Source Diode Forward Current <sup>b</sup>	$I_S$				2.5	A
Drain-Source Diode Forward Voltage <sup>c</sup>	$V_{SD}$	$V_{GS} = 0V, I_S = 2.5A$			1.1	V

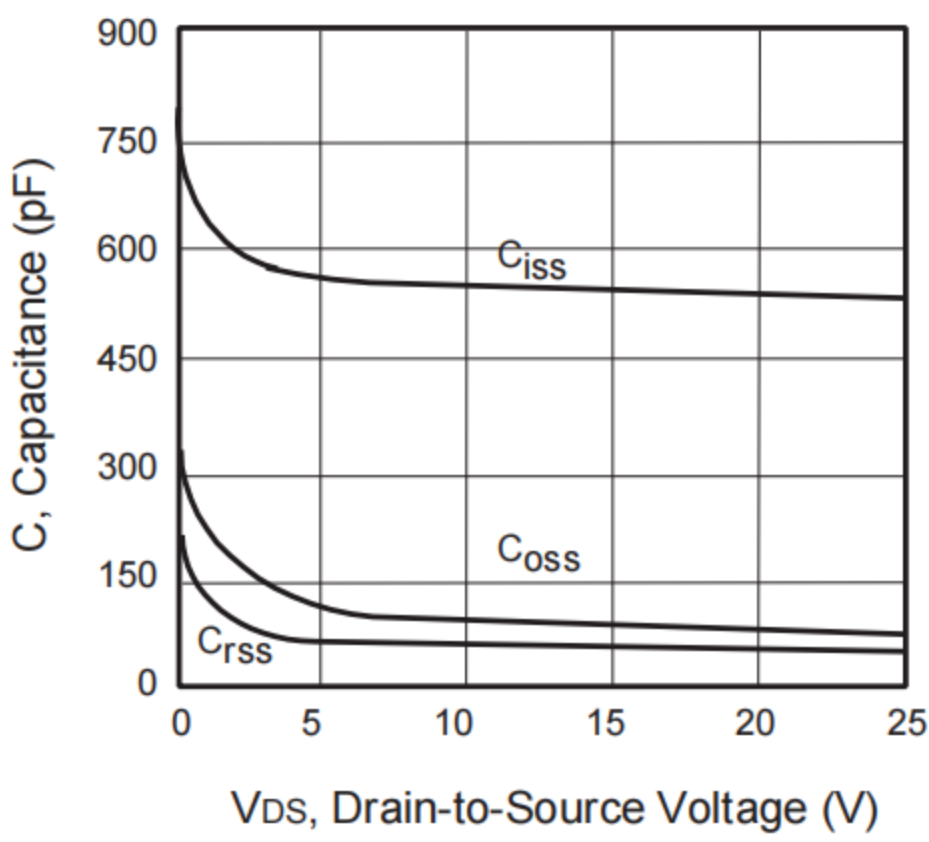
**Typical Electrical and Thermal Characteristics**



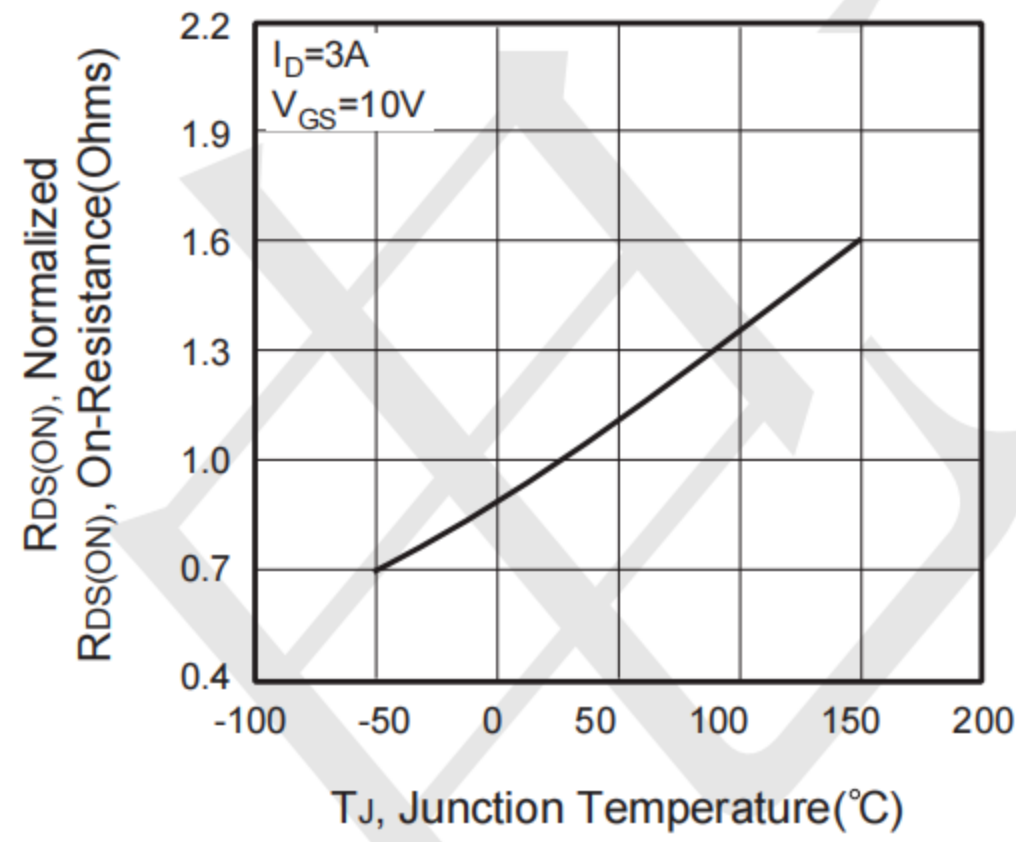
**Figure 1. Output Characteristics**



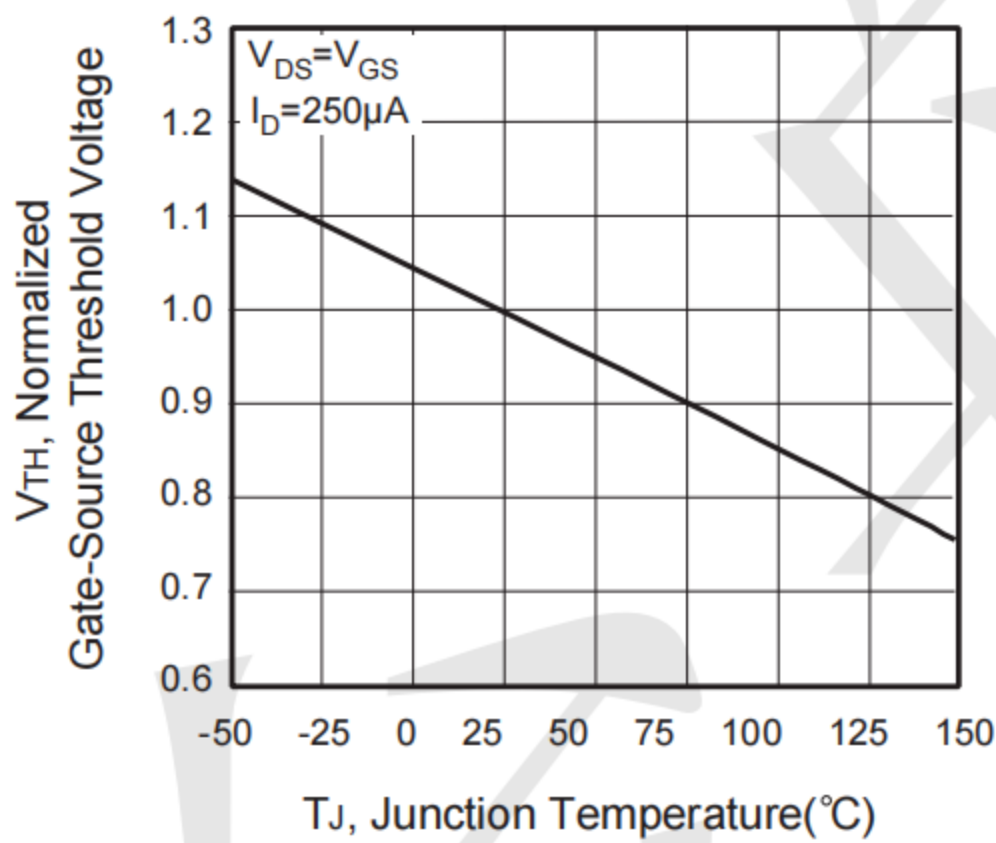
**Figure 2. Transfer Characteristics**



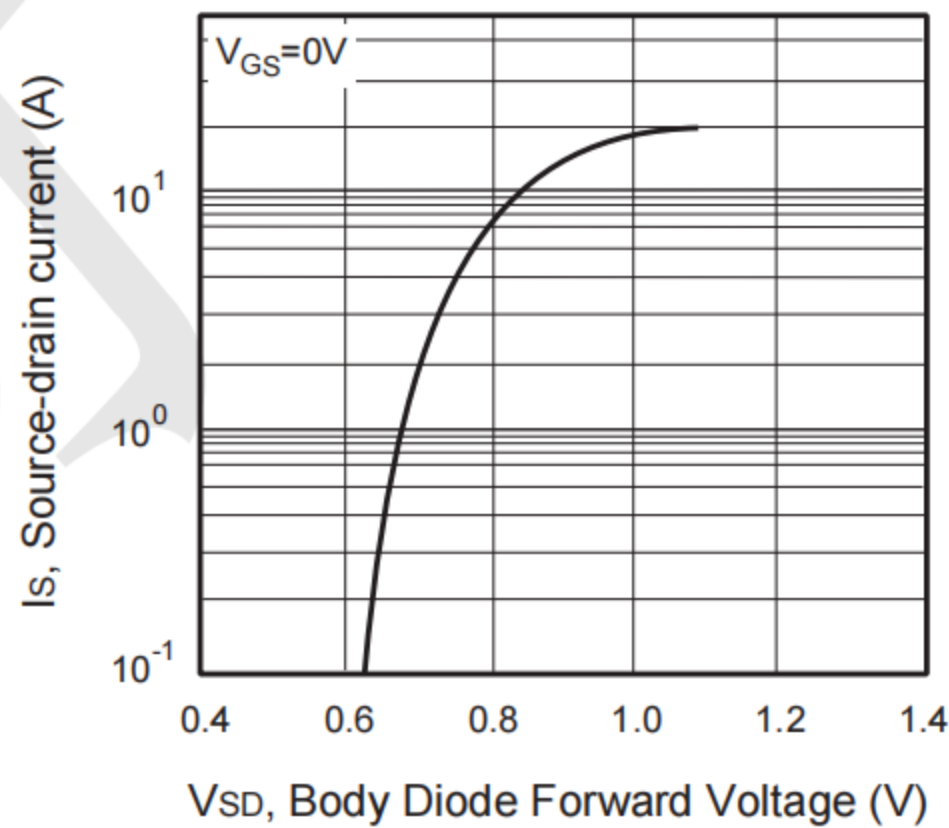
**Figure 3. Capacitance**



**Figure 4. On-Resistance Variation with Temperature**



**Figure 5. Gate Threshold Variation with Temperature**



**Figure 6. Body Diode Forward Voltage Variation with Source Current**

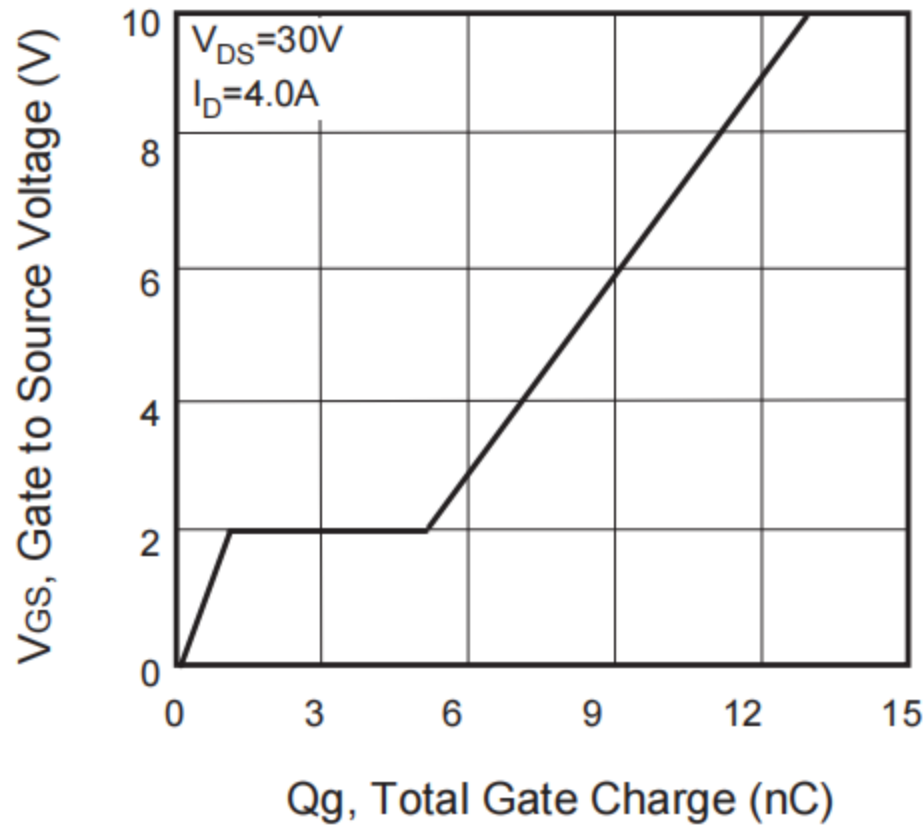


Figure 7. Gate Charge

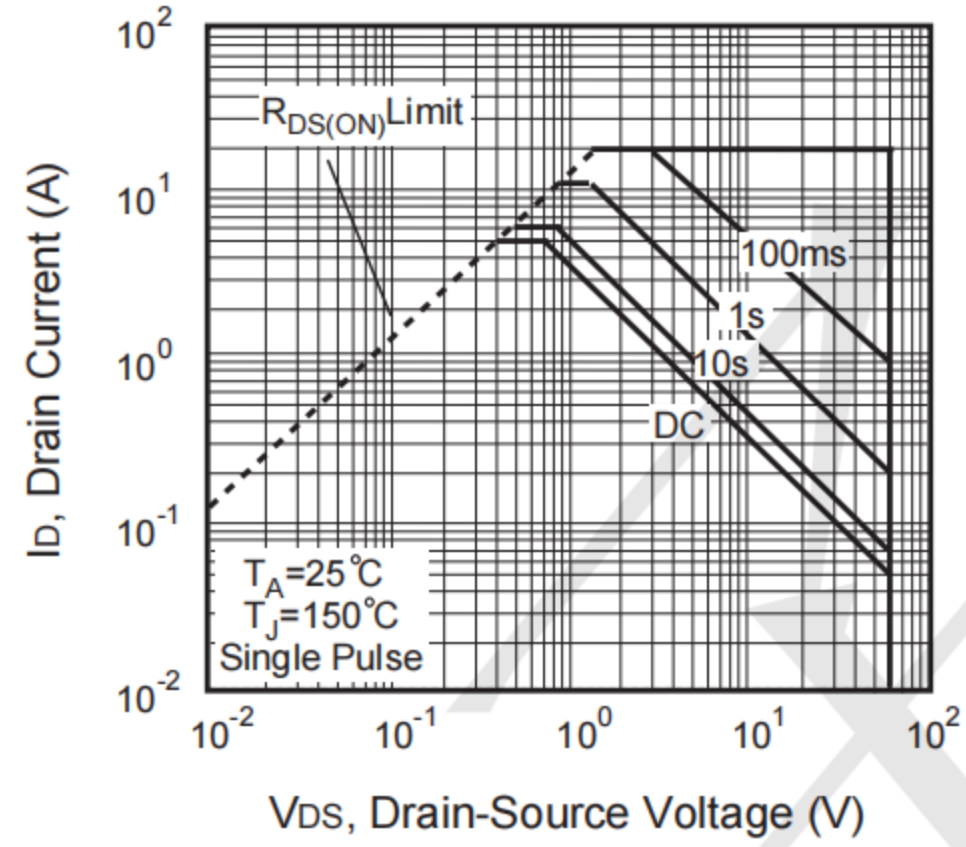


Figure 8. Maximum Safe Operating Area

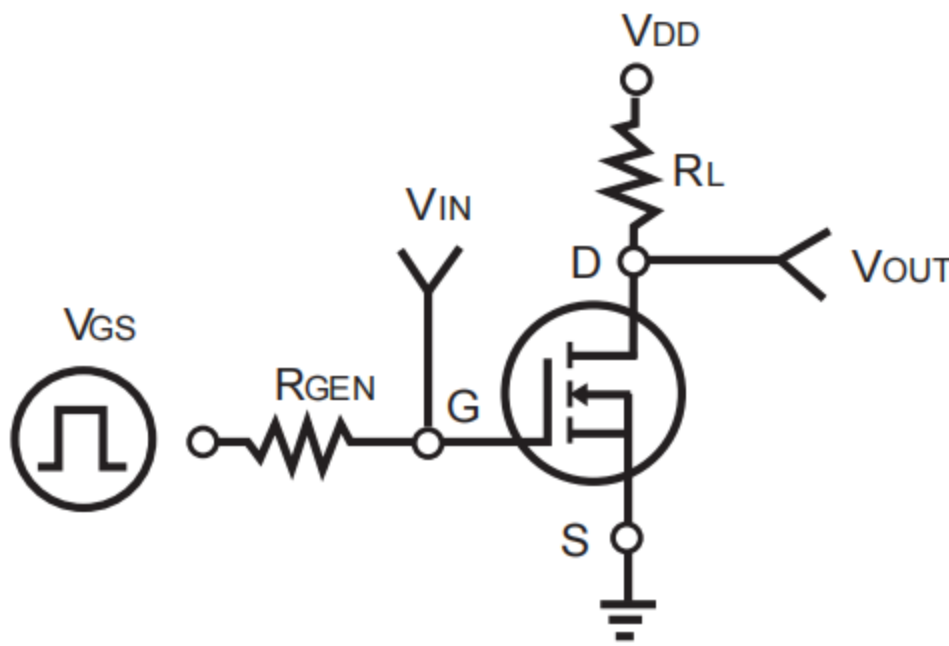


Figure 9. Switching Test Circuit

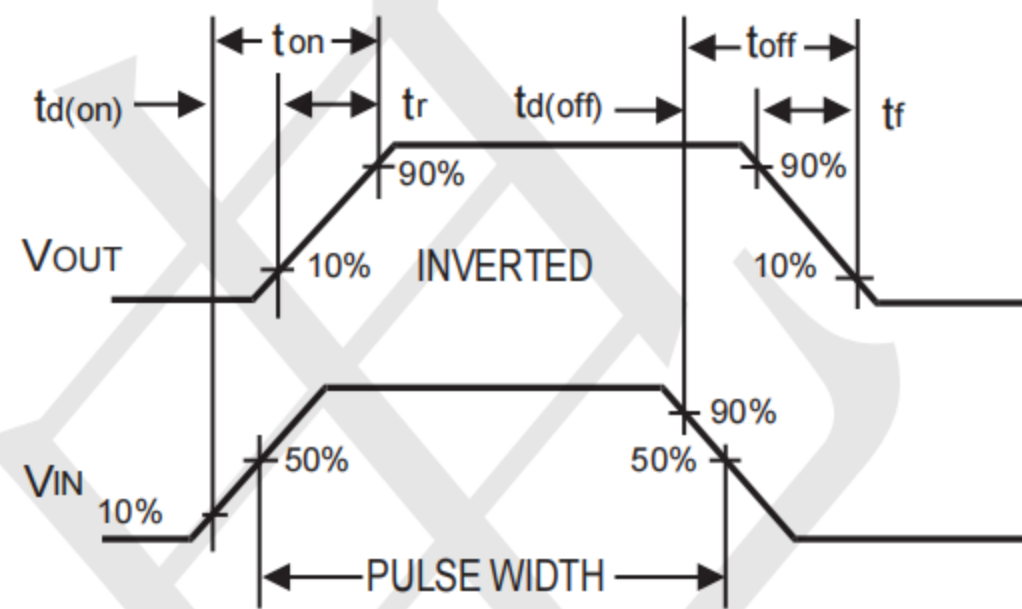


Figure 10. Switching Waveforms

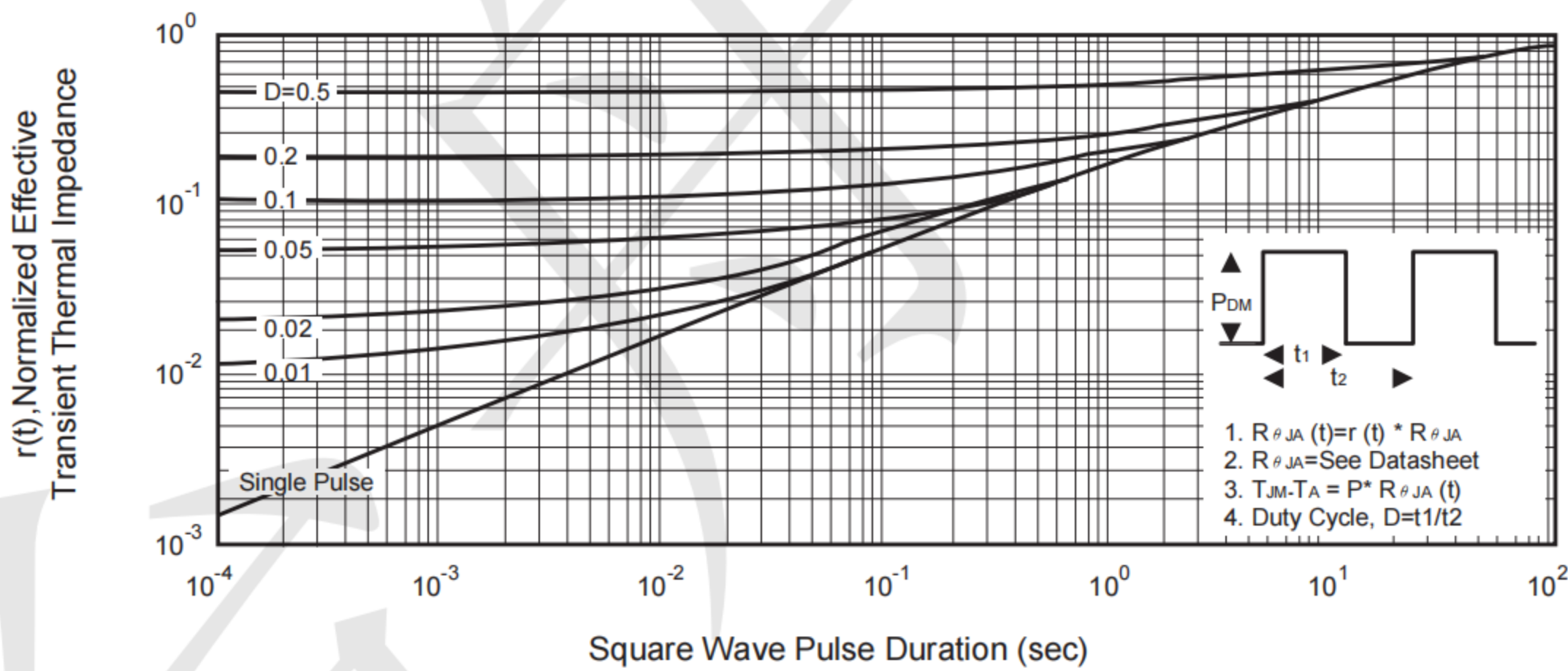
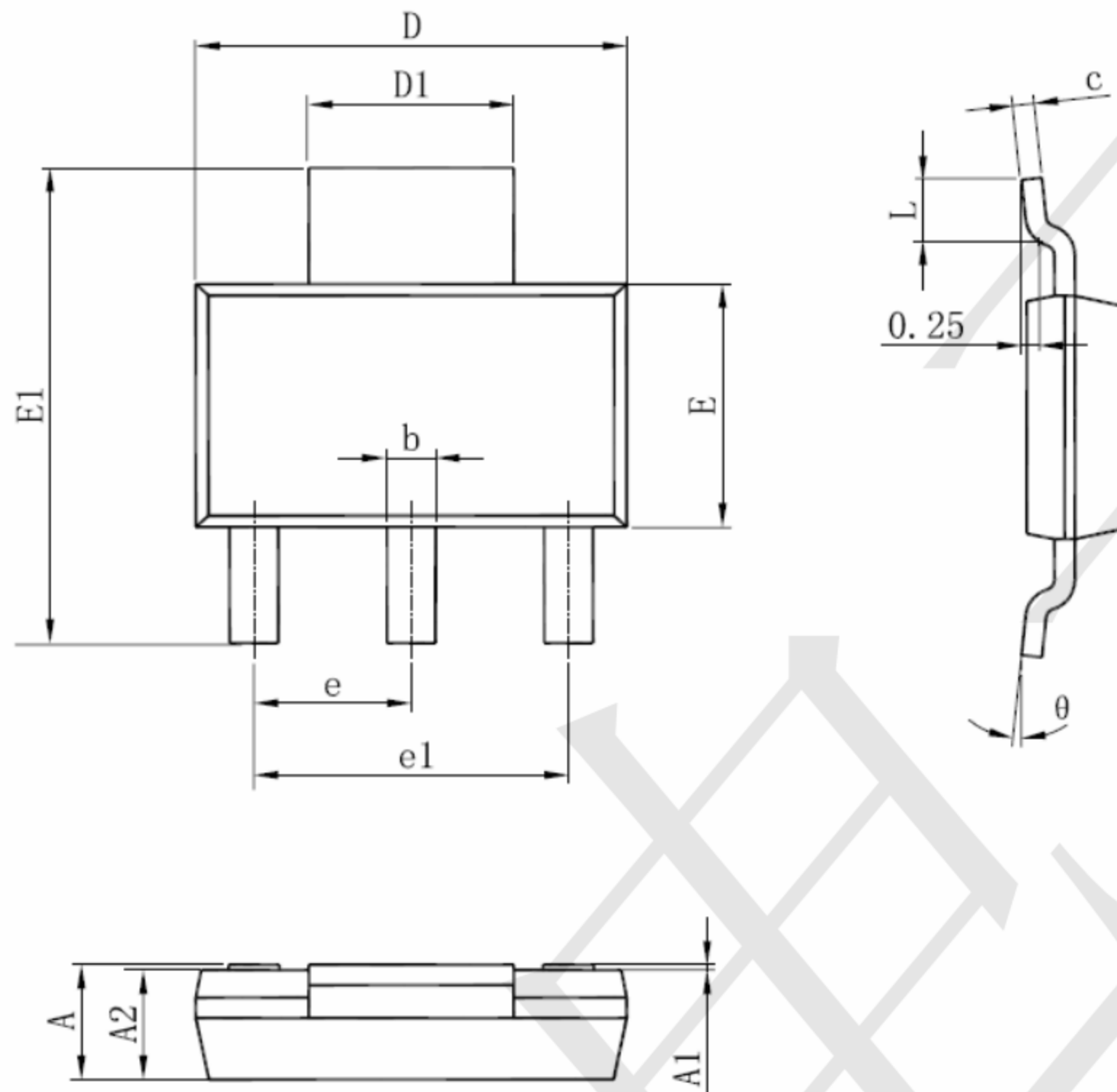


Figure 11. Normalized Thermal Transient Impedance Curve



**SOT-223 Package Information**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.520	1.800	0.060	0.071
A1	0.000	0.100	0.000	0.004
A2	1.500	1.700	0.059	0.067
b	0.660	0.820	0.026	0.032
c	0.250	0.350	0.010	0.014
D	6.200	6.400	0.244	0.252
D1	2.900	3.100	0.114	0.122
E	3.300	3.700	0.130	0.146
E1	6.830	7.070	0.269	0.278
e	2.300(BSC)		0.091(BSC)	
e1	4.500	4.700	0.177	0.185
L	0.900	1.150	0.035	0.045
θ	0°	10°	0°	10°